Unit: mm

TOSHIBA SemiconductorTOSHIBA Field Effect Transistor Silicon N Channel Junction Type

2SK880

Audio Frequency Low Noise Amplifier Applications

- High $|Y_{fs}|$: $|Y_{fs}|$ = 15 mS (typ.) at V_{DS} = 10 V, V_{GS} = 0
- High breakdown voltage: VGDS = -50 V
- Low noise: NF = 1.0dB (typ.)

at VDS = 10 V, ID = 0.5 mA, f = 1 kHz, RG = 1 k Ω

- High input impedance: $I_{GSS} = -1$ nA (max) at $V_{GS} = -30$ V
- · Small package

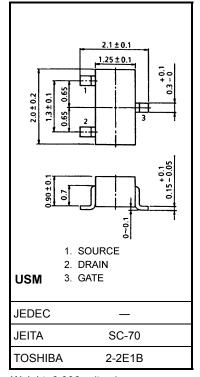
Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Gate-drain voltage	V _{GDS}	-50	V
Gate current	IG	10	mA
Drain power dissipation	P _D	100	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C

Note:

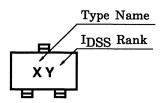
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



Weight: 0.006 g (typ.)

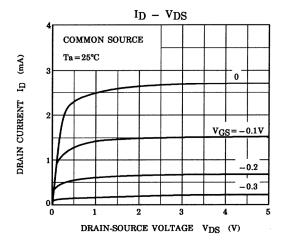
Marking

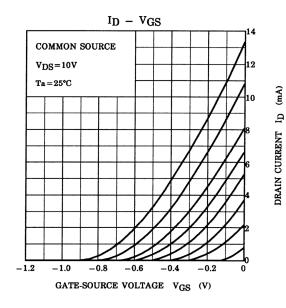


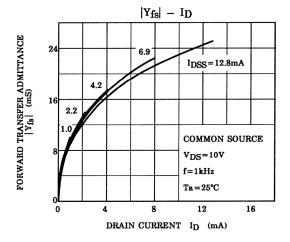
Electrical Characteristics (Ta = 25°C)

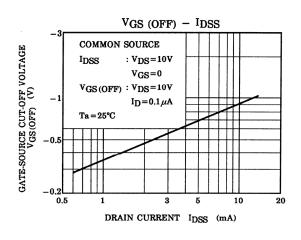
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate cut-off current	I _{GSS}	$V_{GS} = -30 \text{ V}, V_{DS} = 0$	_	_	-1.0	nA
Gate-drain breakdown voltage	V (BR) GDS	$V_{DS} = 0$, $I_G = -100 \mu A$	-50	_	_	V
Drain current	I _{DSS} (Note)	V _{DS} = 10 V, V _{GS} = 0	1.2	_	14.0	mA
Gate-source cut-off voltage	V _{GS} (OFF)	$V_{DS} = 10 \text{ V}, I_D = 0.1 \mu\text{A}$	-0.2	_	-1.5	V
Forward transfer admittance	Y _{fs}	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ kHz}$	4.0	15	_	mS
Input capacitance	C _{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	13	_	pF
Reverse transfer capacitance	C _{rss}	$V_{DG} = 10 \text{ V}, I_D = 0, f = 1 \text{ MHz}$	_	3	_	pF
Noise figure	NF (1)	$V_{DS} = 10 \text{ V}, R_G = 1 \text{ k}\Omega$ $I_D = 0.5 \text{ mA}, f = 10 \text{ Hz}$	_	5	_	-ID
	NF (2)	$V_{DS} = 10 \text{ V}, R_G = 1 \text{ k}\Omega$ $I_D = 0.5 \text{ mA}, f = 1 \text{ kHz}$	_	1	_	dB

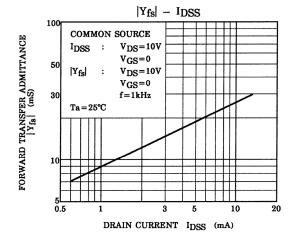
Note: I_{DSS} classification Y: 1.2~3.0 mA, GR: 2.6~6.5 mA, BL: 6.0~14 mA

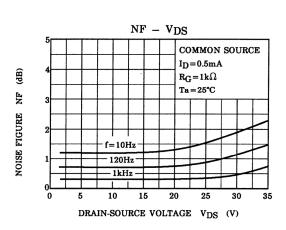




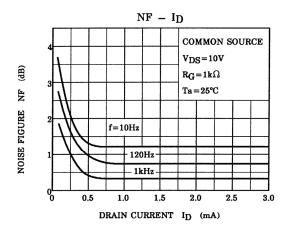


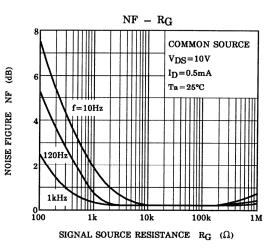


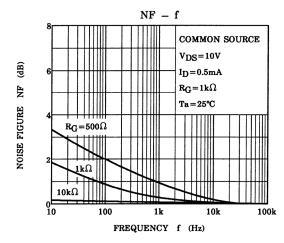


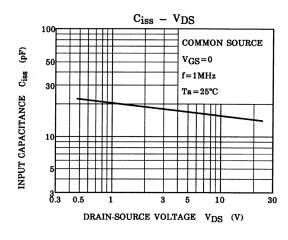


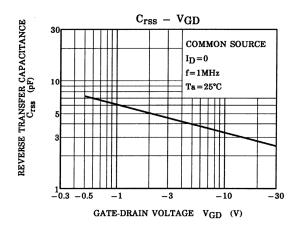
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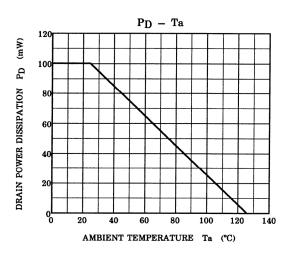












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20070701-EN GENERAL

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